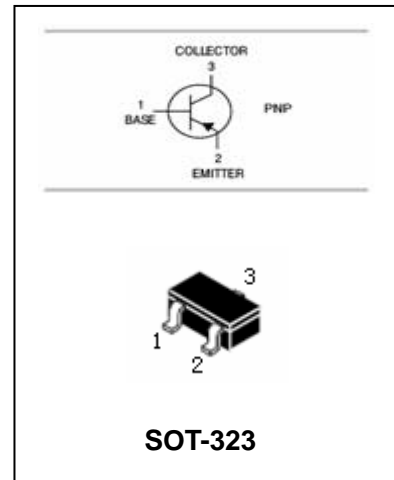


## PNP Silicon Epitaxial Planar Transistor

## MMSTA92

### FEATURES

- Power dissipation.( $P_C=200\text{mW}$ )
- Epitaxial planar die construction.
- Complementary to MMSTA42.
- Also available in lead free version.



### APPLICATIONS

- General purpose application and switching application.

### ORDERING INFORMATION

| Type No. | Marking | Package Code |
|----------|---------|--------------|
| MMSTA92  | K3R     | SOT-323      |

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

| Symbol         | Parameter                        | Value   | Units            |
|----------------|----------------------------------|---------|------------------|
| $V_{CBO}$      | Collector-Base Voltage           | -310    | V                |
| $V_{CEO}$      | Collector-Emitter Voltage        | -305    | V                |
| $V_{EBO}$      | Emitter-Base Voltage             | -5      | V                |
| $I_C$          | Collector Current -Continuous    | -300    | mA               |
| $P_C$          | Collector Dissipation            | 200     | mW               |
| $T_j, T_{stg}$ | Junction and Storage Temperature | -55~150 | $^\circ\text{C}$ |

## PNP Silicon Epitaxial Planar Transistor

## MMSTA92

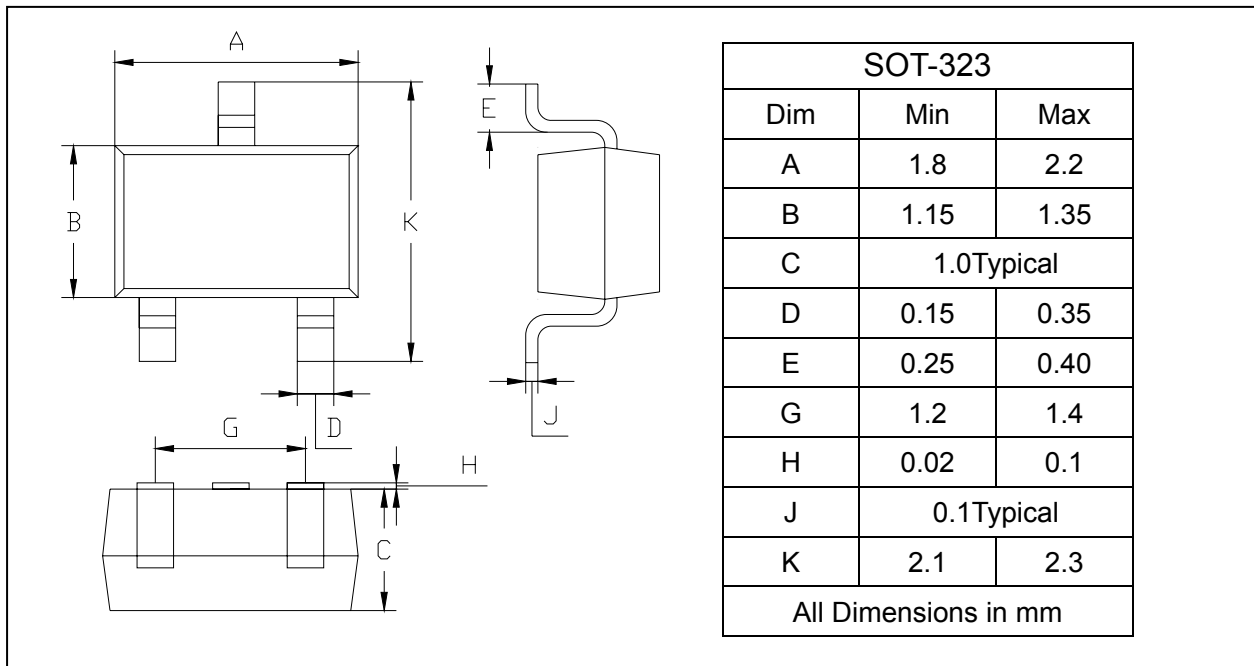
### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

| Parameter                            | Symbol        | Test conditions   | MIN             | TYP | MAX   | UNIT    |
|--------------------------------------|---------------|---|-----------------|-----|-------|---------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C=-100\mu A, I_E=0$  | -310            |     |       | V       |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C=-1mA, I_B=0$   | -305            |     |       | V       |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E=-100\mu A, I_C=0$  | -5              |     |       | V       |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB}=-200V, I_E=0$   |                 |     | -0.25 | $\mu A$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB}=-5V, I_C=0$   |                 |     | -0.1  | $\mu A$ |
| DC current gain                      | $h_{FE}$      | $V_{CE}=-10V, I_C=-1mA$<br>$V_{CE}=-10V, I_C=-10mA$<br>$V_{CE}=-10V, I_C=-80mA$ | 60<br>100<br>60 |     | 200   |         |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C=-20mA, I_B=-2mA$   |                 |     | -0.2  | V       |
| Base-emitter saturation voltage      | $V_{BE(sat)}$ | $I_C=-20mA, I_B=-2mA$   |                 |     | -0.9  | V       |
| Transition frequency                 | $f_T$         | $V_{CE}=-20V, I_C=-10mA,$<br>$f=30MHz$  | 50              |     |       | MHz     |

### PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



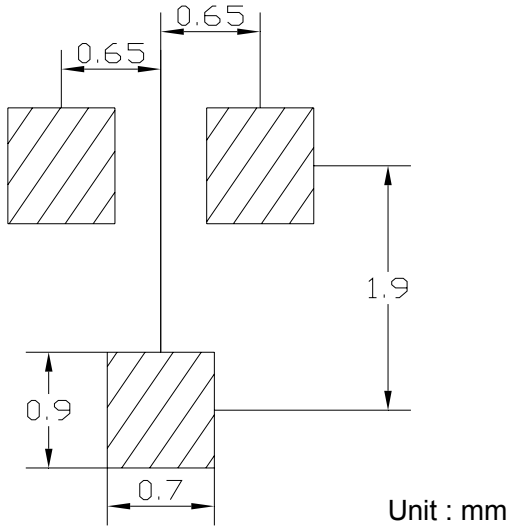
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## PNP Silicon Epitaxial Planar Transistor

## MMSTA92

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### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

| Device  | Package | Shipping       |
|---------|---------|----------------|
| MMSTA92 | SOT-323 | 3000/Tape&Reel |

[www.s-manuals.com](http://www.s-manuals.com)